

1 ABSTRACT OF THE DISCLOSURE

2 The invention encompasses a method of removing at least some of  
3 a material from a semiconductor substrate. A feed gas is fed through  
4 an ozone generator to generate ozone. The feed gas comprises at least  
5 99.999% O<sub>2</sub> (by volume). The ozone, or a fragment of the ozone, is  
6 contacted with a material on a semiconductor substrate to remove at  
7 least some of the material from the semiconductor substrate. The  
8 invention also encompasses another method of removing at least some of  
9 a material from a semiconductor substrate. A mixture of ozone and  
10 organic solvent vapors is formed in a reaction chamber. At least some  
11 of the ozone and solvent vapors are contacted with a material on a  
12 semiconductor substrate to remove at least some of the material from  
13 the semiconductor substrate.  
14  
15  
16  
17  
18  
19  
20  
21  
22  
23